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416 Rec'd PTO 17 MAR 1999

500.36904X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: H. MIURA et al.

Serial No.: Not Yet Assigned

Filed: March 17, 1999

For: *Bad* SEMICONDUCTOR DEVICE AND METHOD OF FABRICATING
THE SAME

#4 1/2 Be
Amclt
JA
Jareda
8-8-00

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

March 17, 1999

Sir:

Prior to examination, please amend the above-identified
application as follows:

IN THE CLAIMS

Please add the following new claim:

SUB
B3
A
-- 9. A method of fabricating a semiconductor device
comprising the steps of:

(a) forming an oxidation prevention film on a
circuit formation surface of a semiconductor substrate,

(b) forming trench regions in said substrate from
said circuit formation surface thereof,

(c) performing a first oxidation to form an oxide
film on said trench regions formed in step (b), and

(d) forming an insulating film inside said oxidized
trench regions so as to completely fill them,
characterized by a further step of: